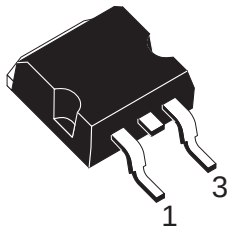
STB8NS25

N-CHANNEL 250V - 0.38Ω - 8A D^2PAK
MESH OVERLAY™ MOSFET

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STB8NS25	250 V	< 0.45 Ω	8 A

- TYPICAL $R_{DS}(on)$ = 0.38 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED



D^2PAK

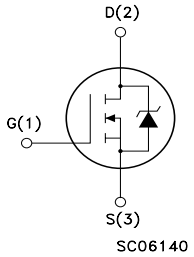
DESCRIPTION

Using the latest high voltage MESH OVERLAY™ process, STMicroelectronics has designed an advanced family of power MOSFETs with outstanding performance. The new patented STrip layout coupled with the Company's proprietary edge termination structure, makes it suitable in coverters for lighting applications.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITH MODE POWER SUPPLIES (SMPS)
- DC-DC CONVERTERS FOR TELECOM, INDUSTRIAL, AND LIGHTING EQUIPMENT

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	250	V
V_{DGR}	Drain-gate Voltage (R_{GS} = 20 kΩ)	250	V
V_{GS}	Gate- source Voltage	± 20	V
I_D (*)	Drain Current (continuos) at T_C = 25°C	8	A
I_D	Drain Current (continuos) at T_C = 100°C	5	A
I_{DM} (•)	Drain Current (pulsed)	32	A
P_{TOT}	Total Dissipation at T_C = 25°C	80	W
	Derating Factor	0.64	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	5	V/ns
T_{stg}	Storage Temperature	–65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

(•)Pulse width limited by safe operating area

(1) I_{SD}≤ 8A, di/dt≤300 A/µs, V_{DD}≤ $V_{(BR)DSS}$, Tj≤T_{jMAX}
(*)Limited only by maximum temperature allowed

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	1.56	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5	°C/W
T_l	Maximum Lead Temperature For Soldering Purpose	300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	8	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 °C, $I_D = I_{AR}$, V_{DD} = 50 V)	300	mJ

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA, V_{GS} = 0	250			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating			1	µA
		V_{DS} = Max Rating, T_C = 125 °C			10	µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ±20V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, I_D = 250µA	2	3	4	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10V, I_D = 4 A		0.38	0.45	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$, I_D = 4A	7	8		S
C_{iss}	Input Capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} = 0		770		pF
C_{oss}	Output Capacitance			118		pF
C_{rss}	Reverse Transfer Capacitance			48		pF

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	V_{DD} = 125 V, I_D = 4 A		13		ns
t_r	Rise Time	R_G = 4.7Ω V_{GS} = 10 V (see test circuit, Figure 3)		18		ns
Q_g	Total Gate Charge	V_{DD} = 200V, I_D = 8 A,		37	51.8	nC
Q_{gs}	Gate-Source Charge	V_{GS} = 10V		5.2		nC
Q_{gd}	Gate-Drain Charge			14.8		nC

SWITCHING OFF

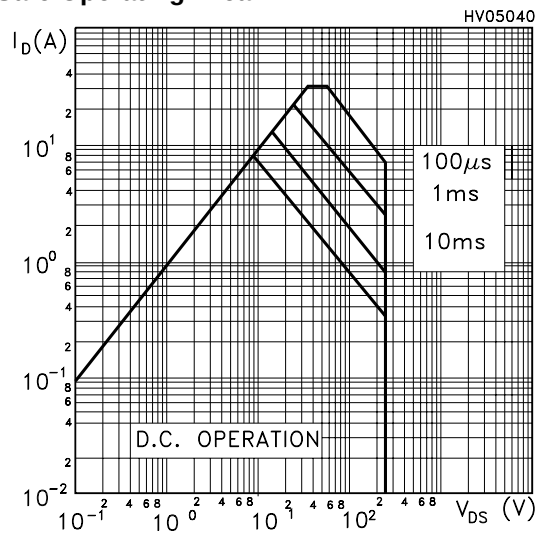
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(Voff)}$	Turn-off- Delay Time	V_{DD} = 125V, I_D = 4 A,		51		ns
t_f	Fall Time	R_G = 4.7Ω, V_{GS} = 10V (see test circuit, Figure 3)		16		ns
$t_{r(Voff)}$	Off-voltage Rise Time	V_{clamp} = 200V, I_D = 8 A,		12.5		ns
t_f	Fall Time	R_G = 4.7Ω, V_{GS} = 10V		12.5		ns
t_c	Cross-over Time	(see test circuit, Figure 5)		28		ns

SOURCE DRAIN DIODE

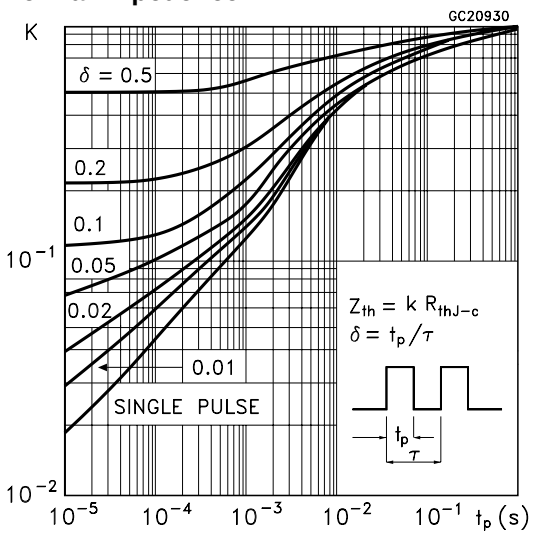
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				8	A
I_{SDM} (2)	Source-drain Current (pulsed)				32	A
V_{SD} (1)	Forward On Voltage	I_{SD} = 8 A, V_{GS} = 0			1.7	V
t_{rr}	Reverse Recovery Time	I_{SD} = 8 A, di/dt = 100A/µs		198		ns
Q_{rr}	Reverse Recovery Charge	V_{DD} = 30V, T_j = 150°C (see test circuit, Figure 5)		1.1		µC
I_{RRM}	Reverse Recovery Current			11.3		A

Note: 1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

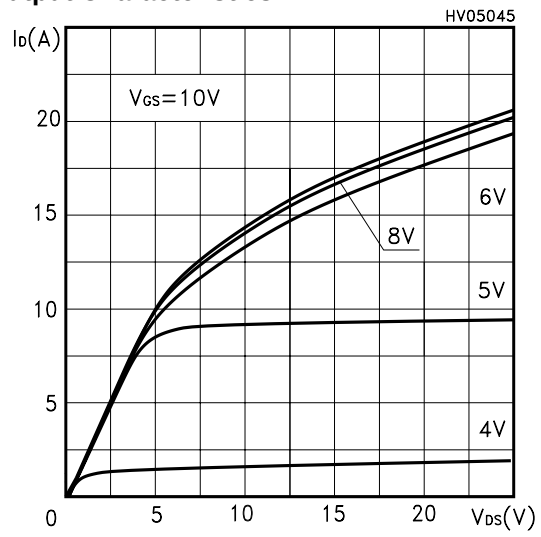
Safe Operating Area



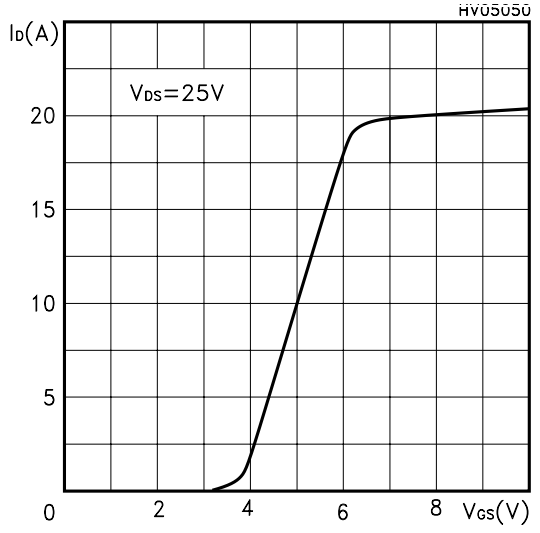
Thermal Impedence



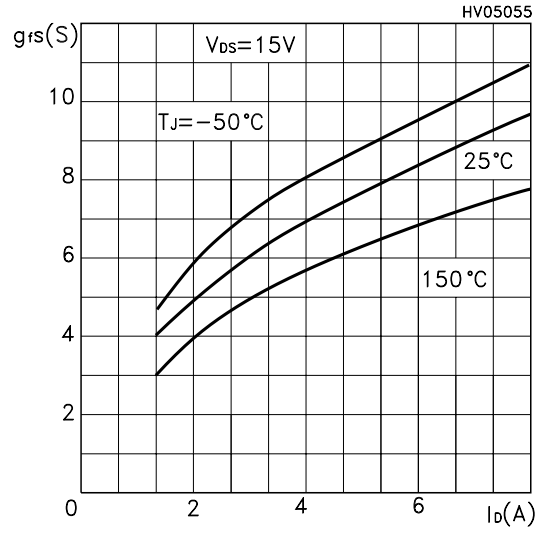
Output Characteristics



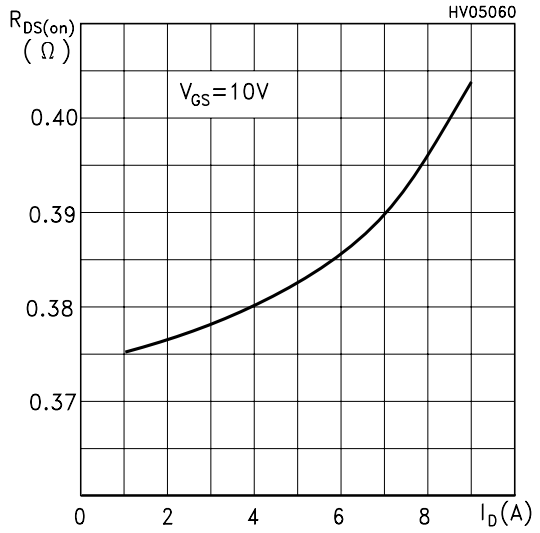
Transfer Characteristics



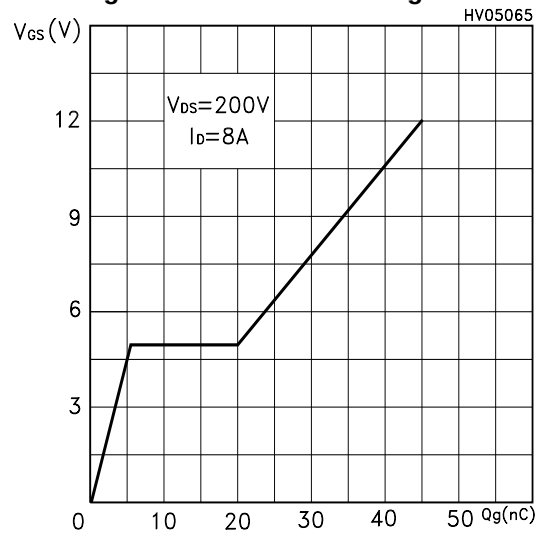
Transconductance



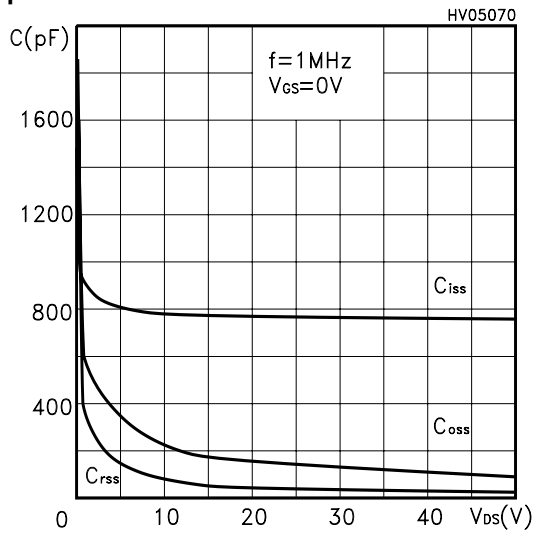
Static Drain-source On Resistance



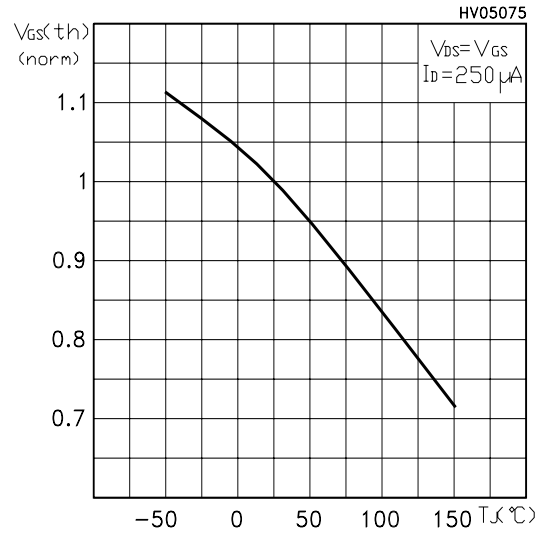
Gate Charge vs Gate-source Voltage



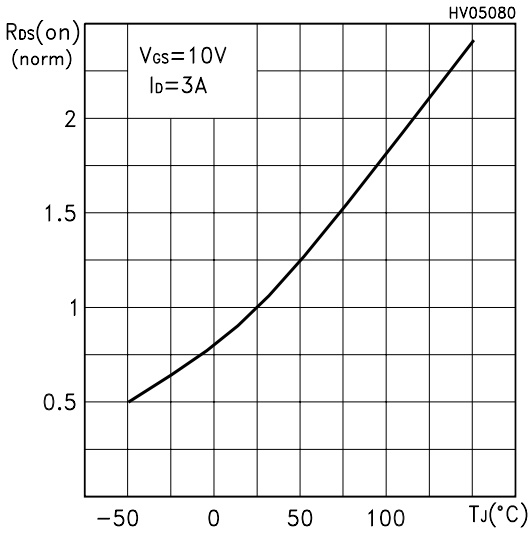
Capacitance Variations



Normalized Gate Thereshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

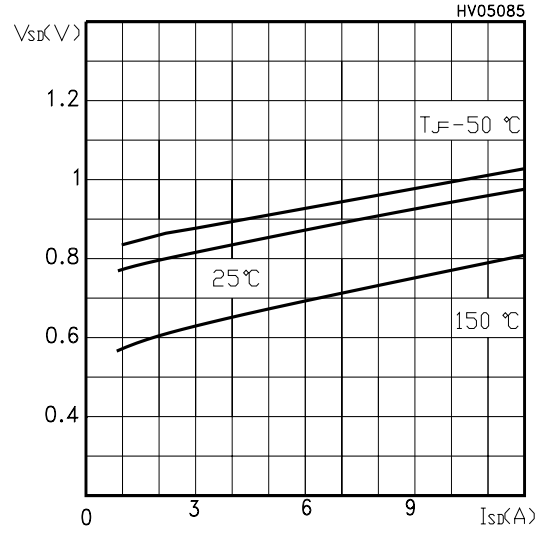


Fig. 1: Unclamped Inductive Load Test Circuit

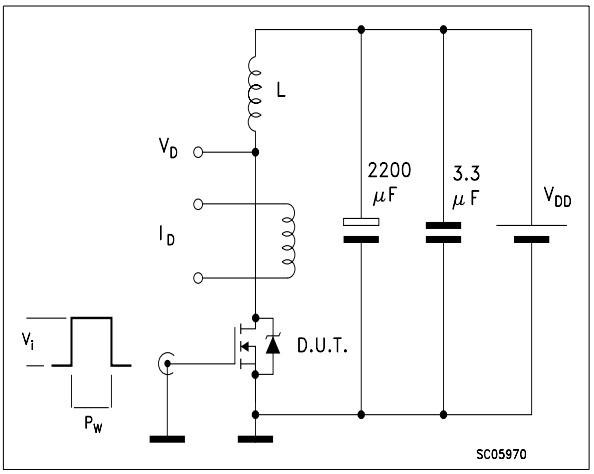


Fig. 2: Unclamped Inductive Waveform

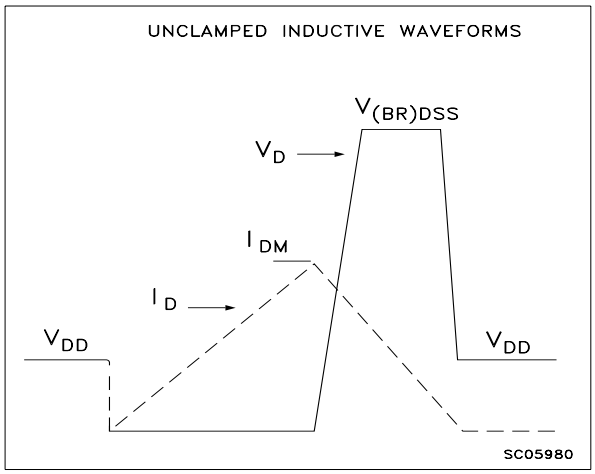


Fig. 3: Switching Times Test Circuit For Resistive Load

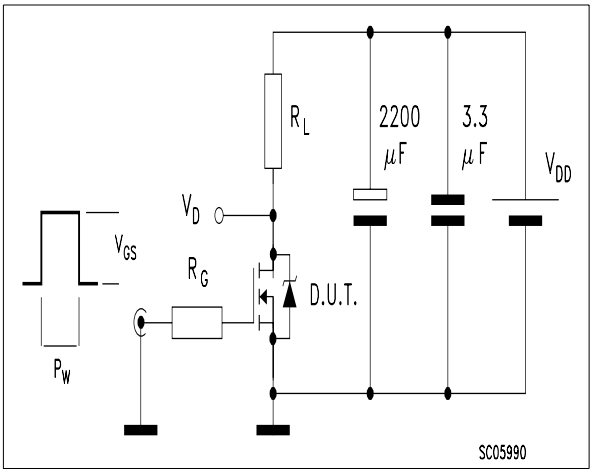


Fig. 4: Gate Charge test Circuit

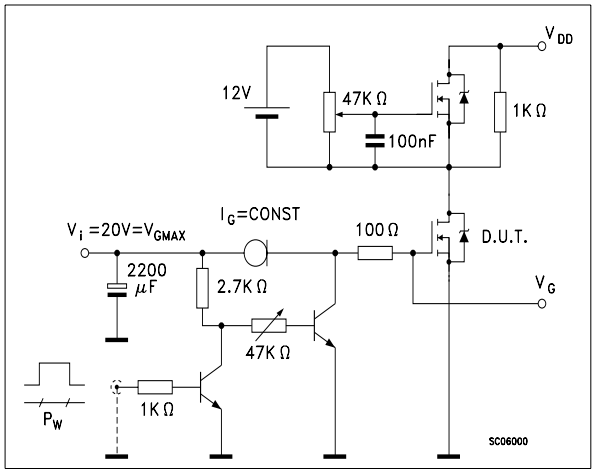
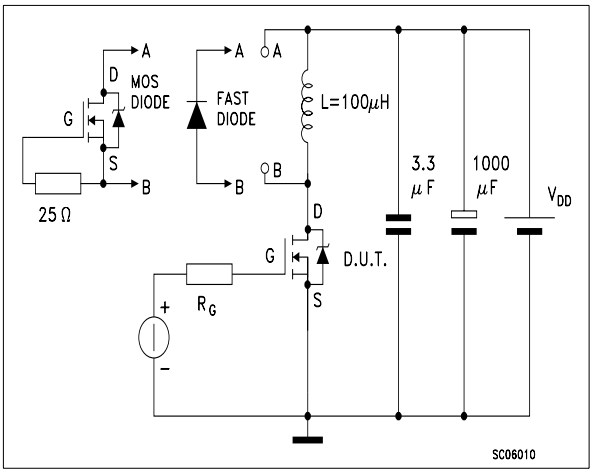
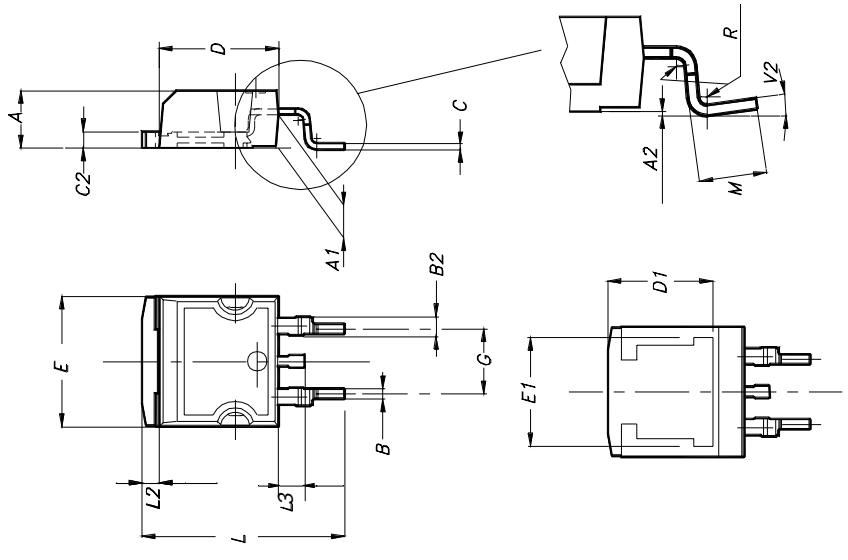


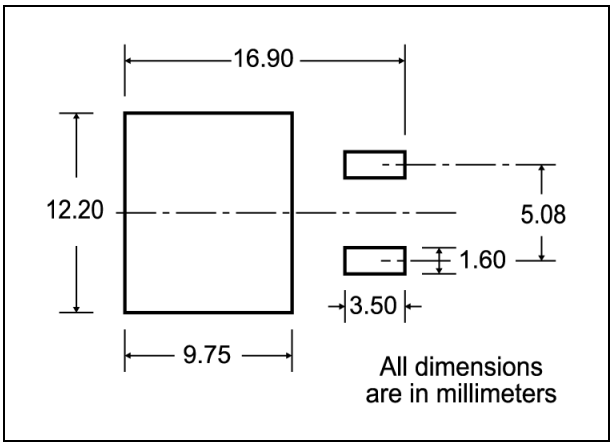
Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times

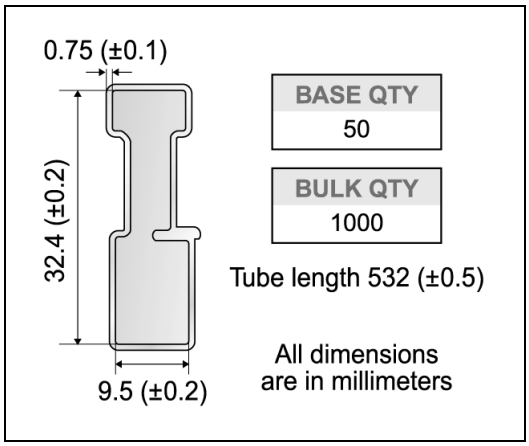


D²PAK MECHANICAL DATA

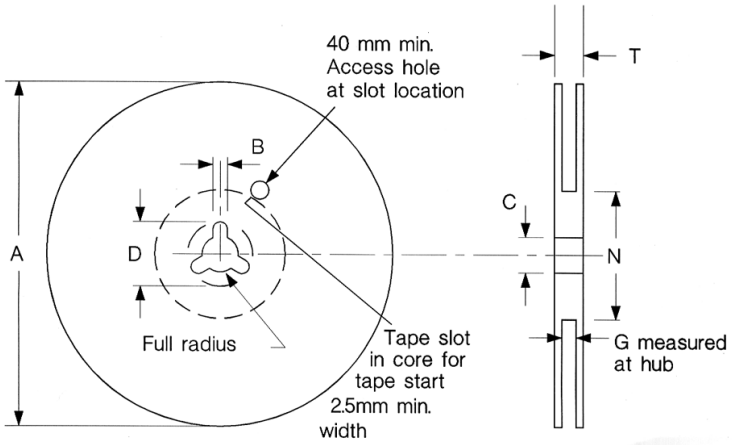
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0º		8º			







TAPE AND REEL SHIPMENT (suffix "T4")*



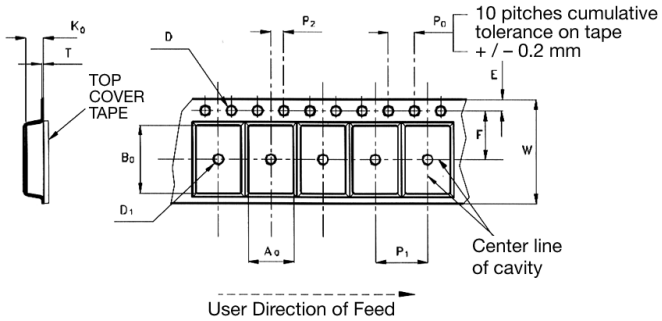
REEL MECHANICAL DATA

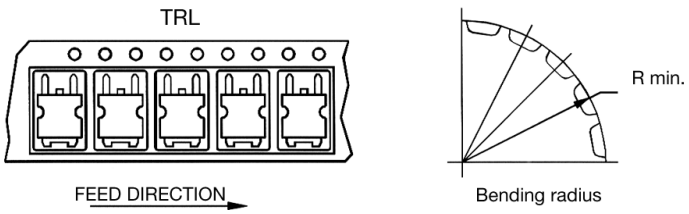
DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956





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